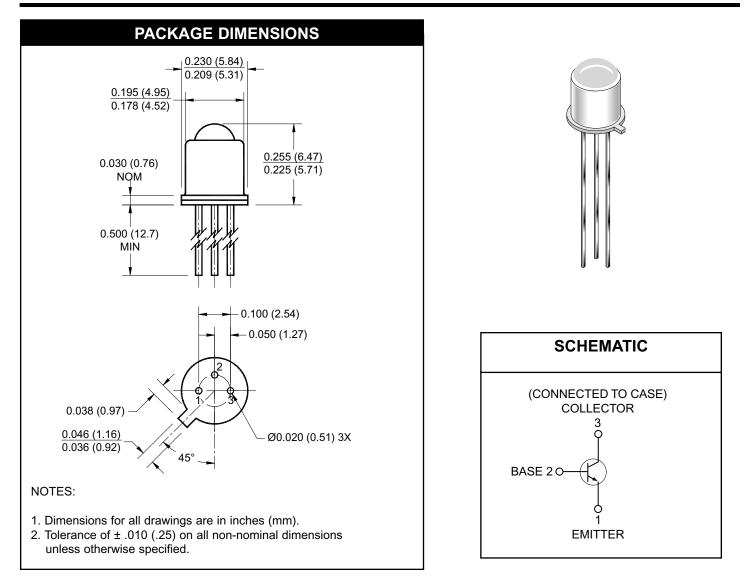


HERMETIC SILICON PHOTOTRANSISTOR

Part Nos. 08 L14G1 and 08 L14G2

L14G1 L14G2 L14G3



DESCRIPTION

The L14G1/L14G2/L14G3 are silicon phototransistors mounted in a narrow angle, TO-18 package.

FEATURES

- · Hermetically sealed package
- Narrow reception angle



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L14G1 L14G2 L14G3

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise specified)							
Parameter	Symbol	Rating	Unit				
Operating Temperature	T _{OPR}	-65 to +125	°C				
Storage Temperature	T _{STG}	-65 to +150	°C				
Soldering Temperature (Iron) ^(3,4,5 and 6)	T _{SOL-I}	240 for 5 sec	°C				
Soldering Temperature (Flow) ^(3,4 and 6)	T _{SOL-F}	260 for 10 sec	°C				
Collector to Emitter Breakdown Voltage	V _{CEO}	45	V				
Collector to Base Breakdown Voltage	V _{CBO}	45	V				
Emitter to Base Breakdwon Voltage	V _{EBO}	5	V				
Power Dissipation (T _A = 25°C) ⁽¹⁾	PD	300	mW				
Power Dissipation (T _C = 25°C) ⁽²⁾	P _D	600	mW				

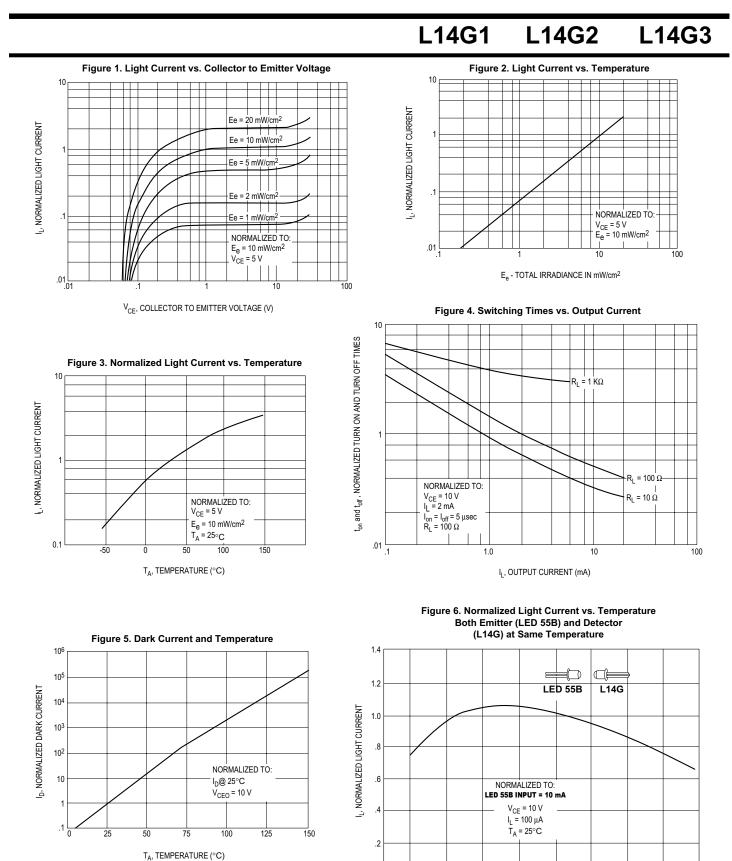
NOTE:

- 1. Derate power dissipation linearly 3.00 mW/°C above 25°C ambient.
- 2. Derate power dissipation linearly 6.00 mW/°C above 25°C case.
- 3. RMA flux is recommended.
- 4. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 5. Soldering iron tip 1/16" (1.6mm) minimum from housing.
- 6. As long as leads are not under any stress or spring tension.
- 7. Light source is a GaAs LED emitting light at a peak wavelength of 940 nm.
- 8. Figure 1 and figure 2 use light source of tungsten lamp at 2870°K color temperature. A GaAs source of 3.0 mW/cm² is approximately equivalent to a tungsten source, at 2870°K, of 10 mW/cm².

ELECTRICAL / OPTICAL CHARACTERISTICS (T _A =25°C) (All measurements made under pulse conditions)							
PARAMETER	TEST CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS	
Collector-Emitter Breakdown	I _C = 10 mA, Ee = 0	BV _{CEO}	45		—	V	
Emitter-Base Breakdown	I _E = 100 μA, Ee = 0	BV _{EBO}	5.0		—	V	
Collector-Base Breakdown	I _C = 100 μA, Ee = 0	BV _{CBO}	45		—	V	
Collector-Emitter Leakage	V _{CE} = 10 V, Ee = 0	I _{CEO}	-		100	nA	
Reception Angle at 1/2 Sensitivity		θ		±10		Degrees	
On-State Collector Current L14G1	Ee = 0.5 mW/cm ² , V _{CE} = 5 V ^(7,8)	I _{C(ON)}	1.0		—	mA	
On-State Collector Current L14G2	Ee = 0.5 mW/cm ² , V _{CE} = 5 V ^(7,8)	I _{C(ON)}	0.5			mA	
On-State Collector Current L14G3	Ee = 0.5 mW/cm ² , V _{CE} = 5 V ^(7,8)	I _{C(ON)}	2.0			mA	
Turn-On Time	I_{c} = 2 mA, V_{cc} = 10 V, R_{L} =100 Ω	t _{on}		8		μs	
Turn-Off Time	$I_{\rm C}$ = 2 mA, $V_{\rm CC}$ = 10 V, $R_{\rm L}$ =100 Ω	t _{off}		7		μs	
Saturation Voltage	$I_{\rm C}$ = 1.0 mA, Ee = 3.0 mW/cm ^{2(7,8)}	V _{CE(SAT)}	_		0.40	V	



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 T_A , TEMPERATURE (°C)



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L14G1 L14G2 L14G3

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